

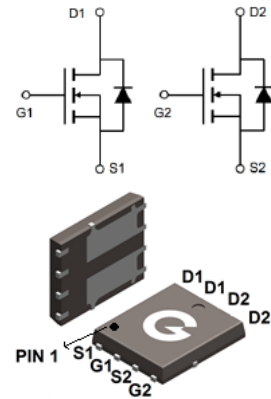
Features

- Ultra-low on-resistance and gate-charge
- Advanced shielded-gate technology

HF

Mechanical Data

- Case: PDFN5x6-8LC
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



PDFN5x6-8LC

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
GBLN4401-5DL8	PDFN5x6-8LC	5000 pcs / Tape & Reel	GBLN4401

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	40	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (T _C = 25°C) *1	I _D	48	A
Continuous Drain Current (T _C = 100°C) *1		31	A
Continuous Drain Current (T _A = 25°C) *2, 3		14	A
Continuous Drain Current (T _A = 100°C) *2, 3		9	A
Pulsed Drain Current *4	I _{DM}	180	A
Single Pulse Avalanche Energy *5, 6	E _{AS}	11	mJ

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation (T _C = 25°C)	P _D	31	W
Thermal Resistance Junction-to-Case	R _{θJC}	3.9	°C/W
Thermal Resistance Junction-to-Air *3	R _{θJA}	47	°C/W
Operating Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 40V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
$R_{DS(ON)}$	Static Drain-Source On-resistance	$V_{GS} = 10V, I_D = 10A$	-	6.8	7.5	m Ω
		$V_{GS} = 4.5V, I_D = 10A$	-	9.2	12.5	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.6	2.5	V
R_G	Gate Resistance	$V_{GS} = 0V, f = 1MHz$	-	3.8	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{GS} = 0V$	-	825	-	pF
C_{OSS}	Output Capacitance	$V_{DS} = 20V$	-	377	-	
C_{RSS}	Reverse Transfer Capacitance	$f = 1.0MHz$	-	28	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD} = 20V$	-	8	-	ns
t_r	Turn-on Rise Time	$V_{GS} = 10V$	-	6	-	
$t_{d(OFF)}$	Turn-Off Delay Time	$R_G = 3\Omega$	-	16	-	
t_f	Turn-Off Fall Time	$I_D = 20A$	-	4	-	
Q_G	Total Gate-Charge	$V_{DD} = 20V$	-	17	-	nC
Q_{GS}	Gate to Source Charge	$V_{GS} = 10V$	-	3.1	-	
Q_{GD}	Gate to Drain (Miller) Charge	$I_D = 15A$	-	2	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage	$I_S = 10A, V_{GS} = 0V$	-	0.8	-	V
t_{rr}	Reverse Recovery Time	$I_S = 20A, V_{GS} = 0V$	-	36	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 100A/\mu s$	-	21	-	nC

Notes:

1. Rated according to $R_{\theta JC}$
2. Rated according to $R_{\theta JA}$
3. Surface-mounted on 1 inch² FR4 board, 2 oz Cu
4. Limited by maximum T_J
5. Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 30V$, $V_{GS} = 10V$, $L = 0.1mH$
6. TBC: To be confirmed

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

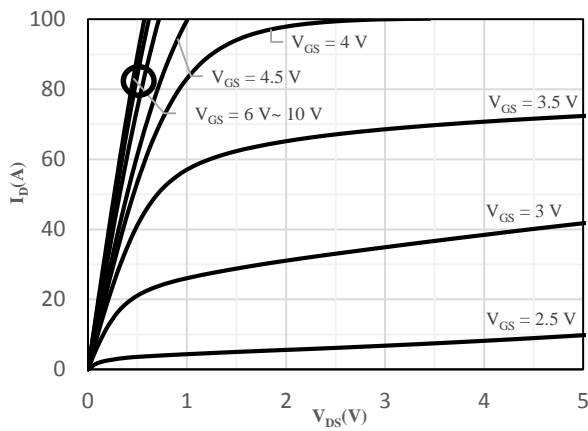


Fig 1 Typical Output Characteristics

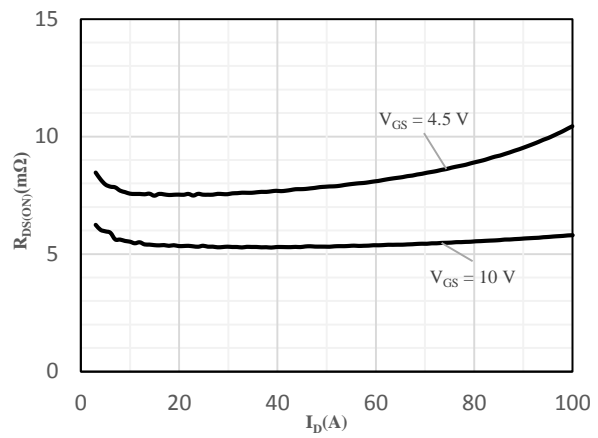


Fig 2 On-Resistance vs. Drain Current and Gate Voltage

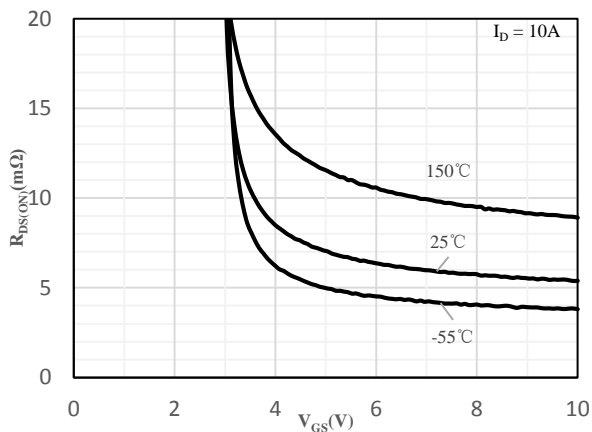


Fig 3 On-Resistance vs. Gate-Source Voltage

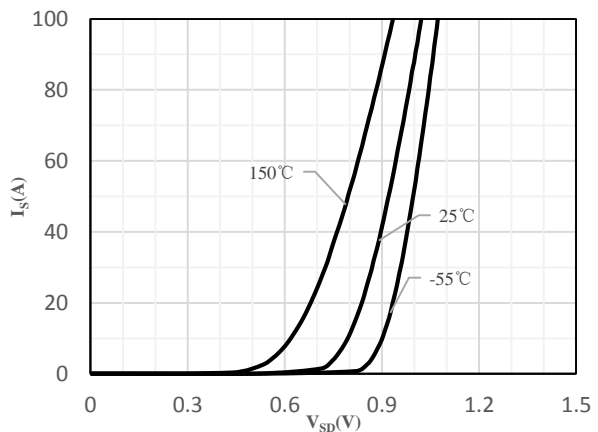


Fig 4 Body-Diode Characteristics

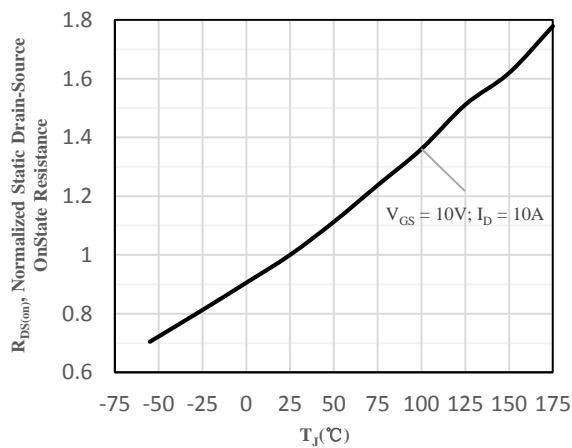


Fig 5 On-Resistance vs. Junction Temperature

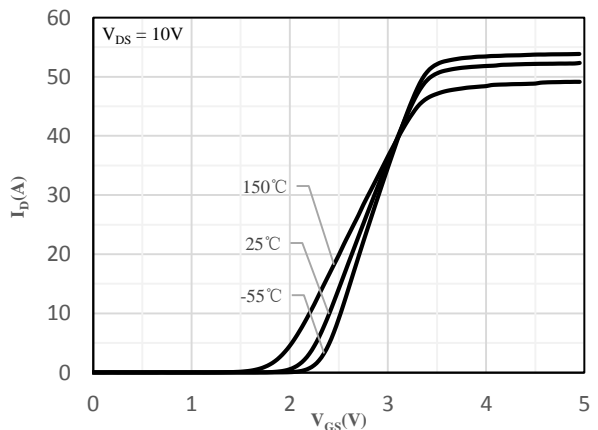


Fig 6 Transfer Characteristics

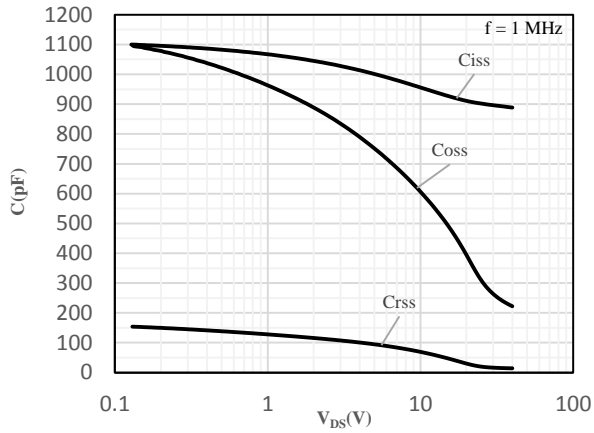


Fig 7 Capacitance Characteristics

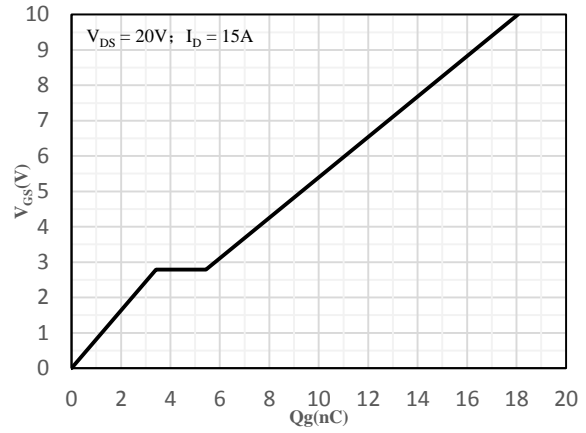


Fig 8 Gate-Charge Characteristics

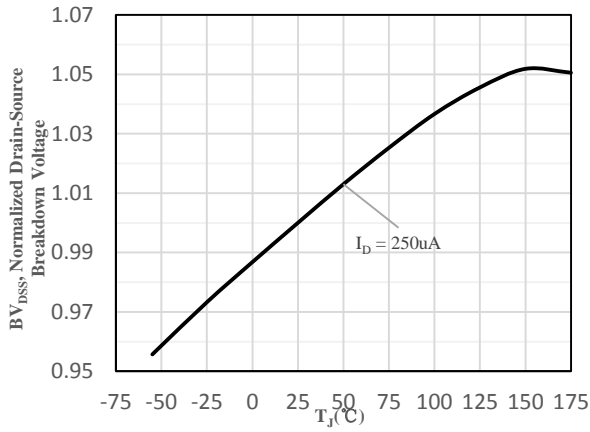


Fig 9 Normalized Breakdown Voltage vs. Junction Temperature

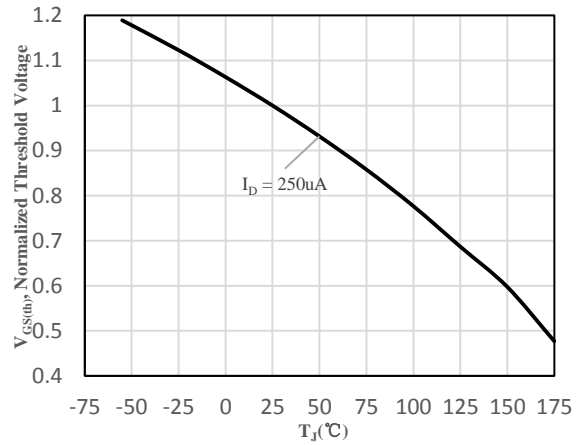


Fig 10 Normalized $V_{GS(th)}$ vs. Junction Temperature

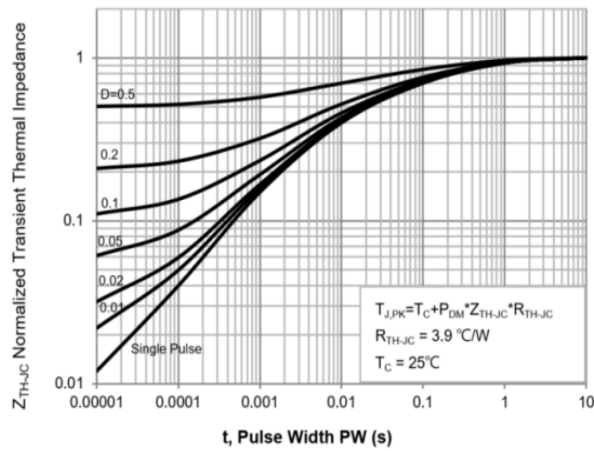


Fig 11 Normalized Transient Thermal Impedance

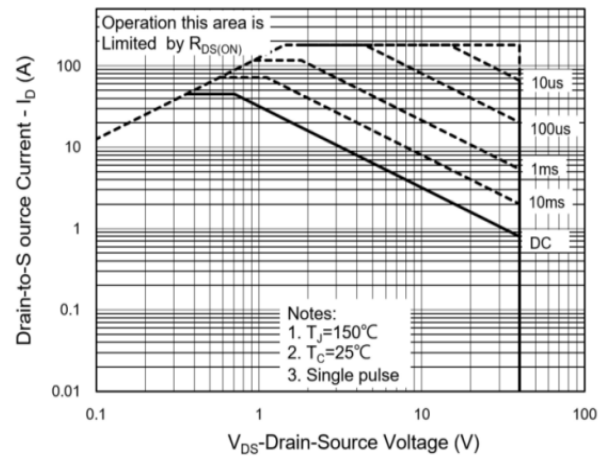
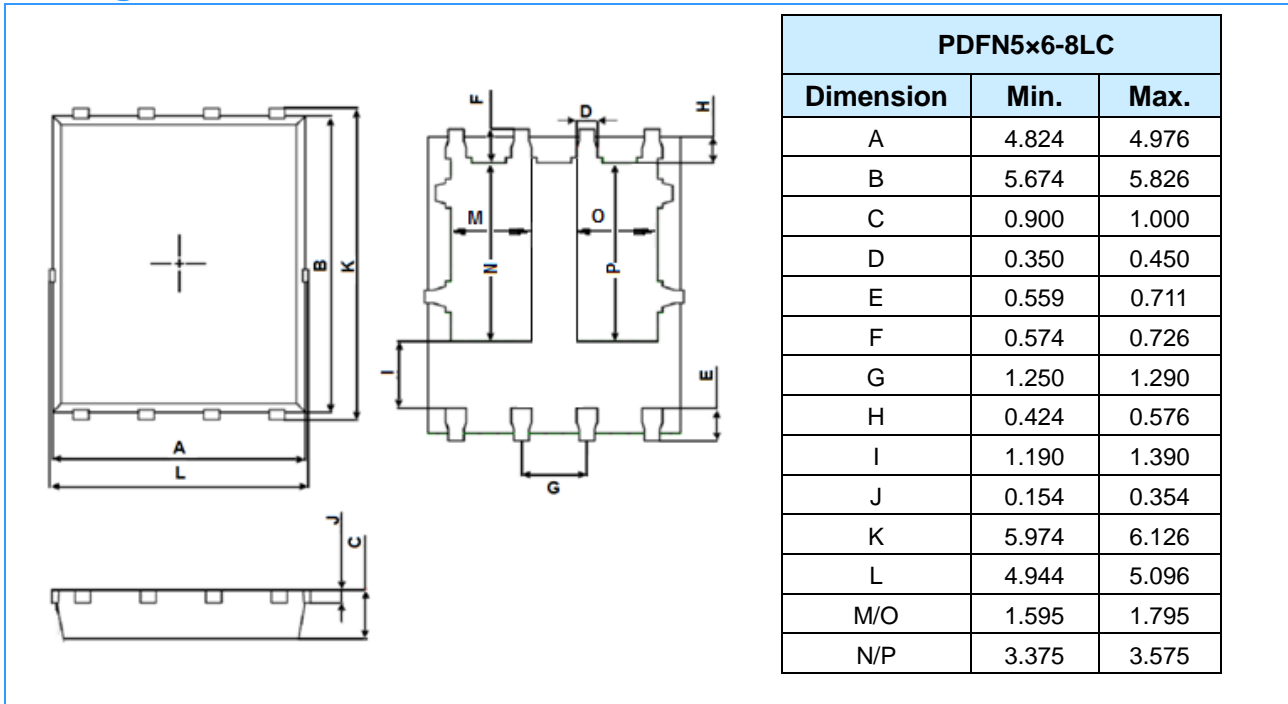
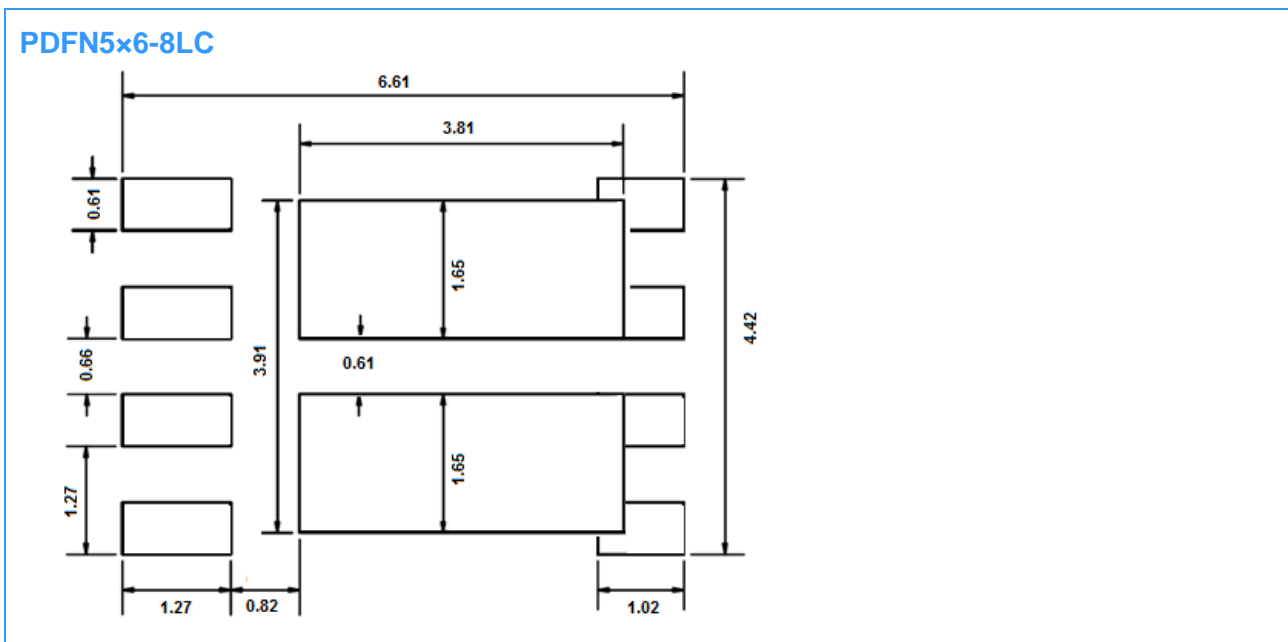


Fig 12 Maximum Safe Operating Area

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



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